

$V_{DS}$	-20V
$I_D$	-7A
$R_{DS(ON)}$ ( at $V_{GS}=-4.5V$ )	36.5mohm
$R_{DS(ON)}$ ( at $V_{GS}=-2.5V$ )	46.5mohm
$R_{DS(ON)}$ ( at $V_{GS}=-1.8V$ )	60.5mohm

Trench Power LV MOSFET technology  
High density cell design for Low  $R_{DS(ON)}$   
High Speed switching

Battery protection  
Power management  
Load switch

( $T_A=25$  unless otherwise noted)

Drain-source Voltage		$V_{DS}$	-20	V
Gate-source Voltage		$V_{GS}$	$\pm 10$	V
Drain Current	$T_C=25$ @ Steady State	$I_D$	-7	A
	$T_C=70$ @ Steady State		-5.6	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	-28	A
Total Power Dissipation @ $T_C=25$ <sup>C</sup>		$P_D$	2.2	W

Thermal Resistance Junction-to-Ambient @ Steady State <sup>D</sup>

$R_{JA}$

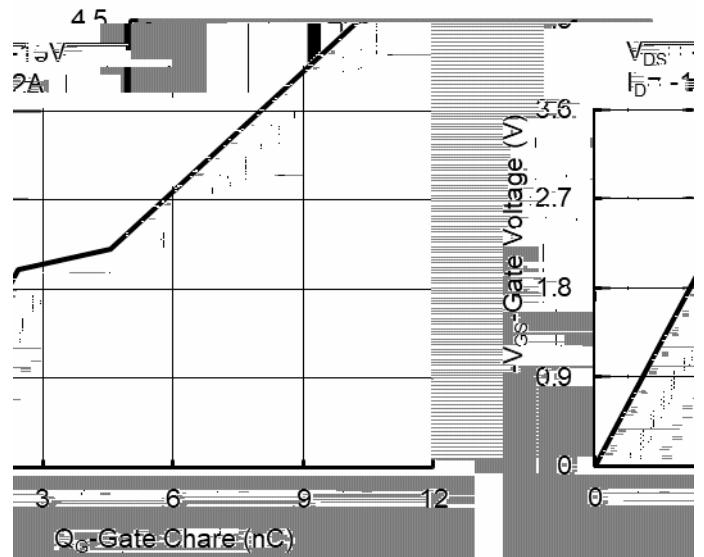
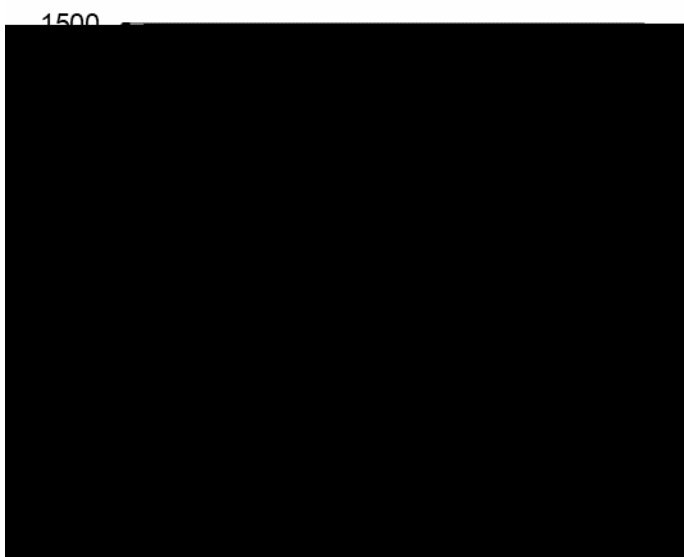
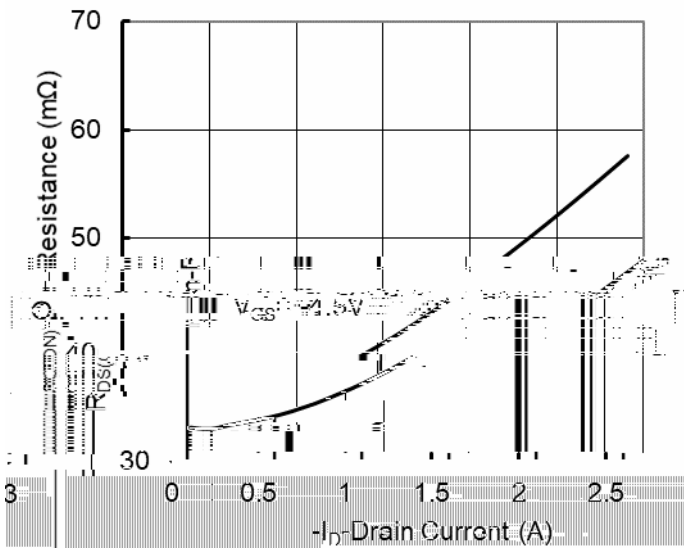
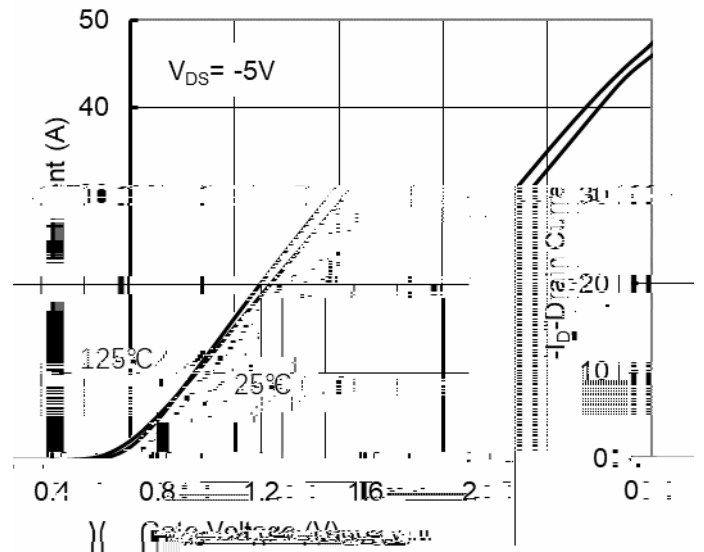
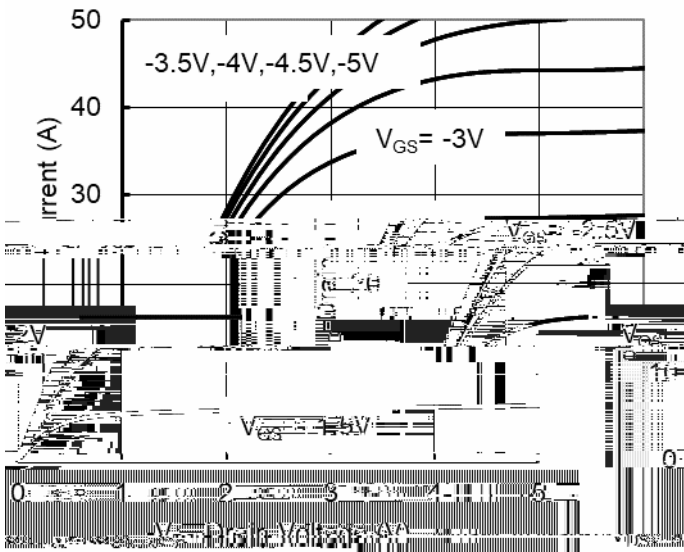
(Example)

YJQ4666B	F1	..G66B	3000	30000	120000	7 " reel
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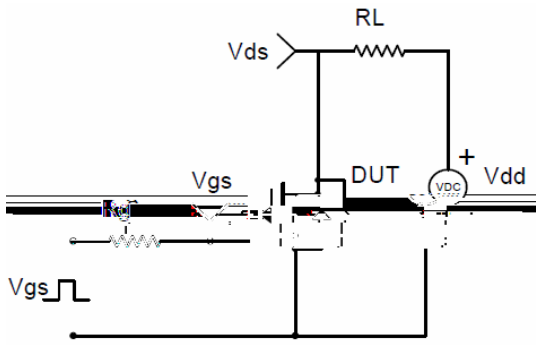


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(T<sub>J</sub>=25











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